FAIRCHILD SEMICONDUCTOR®

June 2007

UniFET™

FDB28N30

N-Channel MOSFET

300V, 28A, 0.129Ω

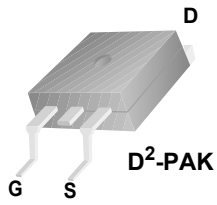
Features

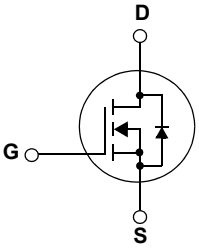
- $R_{DS(on)}$ = 0.108Ω (Typ.)@ V_{GS} = 10V, I_D = 14A
- Low gate charge (Typ. 39nC)
- Low C_{rss} (Typ. 35pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability
- RoHS compliant

Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficient switched mode power supplies and active power factor correction.





MOSFET Maximum Ratings T_C = 25°C unless otherwise noted*

Symbol	Parameter			Ratings	Units
V_{DSS}	Drain to Source Voltage			300	V
V_{GSS}	Gate to Source Voltage			±30	V
I_D	Drain Current	-Continuous (T_C = 25°C)		28	A
		-Continuous (T_C = 100°C)		19	
I_{DM}	Drain Current	- Pulsed	(Note 1)	112	A
E_{AS}	Single Pulsed Avalanche Energy		(Note 2)	588	mJ
I_{AR}	Avalanche Current		(Note 1)	28	A
E_{AR}	Repetitive Avalanche Energy		(Note 1)	25	mJ
dv/dt	Peak Diode Recovery dv/dt		(Note 3)	4.5	V/ns
P_D	Power Dissipation	(T_C = 25°C)		250	W
		- Derate above 25°C		2.0	W/°C
T_J, T_{STG}	Operating and Storage Temperature Range			-55 to +150	°C
T_L	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds			300	°C

Thermal Characteristics

Symbol	Parameter	Ratings	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case	0.5	°C/W
$R_{\theta JA}$*	Thermal Resistance, Junction to Ambient*	40	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	62.5	

*When mounted on the minimum pad size recommended (PCB Mount)

Package Marking and Ordering Information $T_C = 25^oC$ unless otherwise noted

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDB28N30	FDB28N30TM	D2-PAK	330mm	24mm	800

Electrical Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
Off Characteristics						
BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250\mu A$, $V_{GS} = 0V$, $T_J = 25^oC$	300	-	-	V
ΔBV_{DSS} / ΔT_J	Breakdown Voltage Temperature Coefficient	$I_D = 250\mu A$, Referenced to 25^oC	-	0.4	-	$V/^oC$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 300V$, $V_{GS} = 0V$	-	-	1	μA
		$V_{DS} = 240V$, $T_C = 125^oC$	-	-	10	
I_{GSS}	Gate to Body Leakage Current	$V_{GS} = \pm 30V$, $V_{DS} = 0V$	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250\mu A$	3.0	-	5.0	V
$R_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10V$, $I_D = 14A$	-	0.108	0.129	Ω
g_{FS}	Forward Transconductance	$V_{DS} = 40V$, $I_D = 14A$ (Note 4)	-	24.8	-	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS} = 25V$, $V_{GS} = 0V$, f = 1MHz	-	1690	2250	pF
C_{oss}	Output Capacitance		-	305	405	pF
C_{rss}	Reverse Transfer Capacitance		-	35	50	pF
Q_g	Total Gate Charge at 10V	$V_{DS} = 240V$, $I_D = 28A$, $V_{GS} = 10V$ (Note 4, 5)	-	39	50	nC
Q_{gs}	Gate to Source Gate Charge		-	12	-	nC
Q_{gd}	Gate to Drain “Miller” Charge		-	17	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 150V$, $I_D = 28A$, $R_G = 25\Omega$ (Note 4, 5)	-	35	80	ns
t_r	Turn-On Rise Time		-	135	280	ns
$t_{d(off)}$	Turn-Off Delay Time		-	79	168	ns
t_f	Turn-Off Fall Time		-	69	148	ns
Drain-Source Diode Characteristics						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	28	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	112	A
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS} = 0V$, $I_{SD} = 28A$	-	-	1.4	V
t_{rr}	Reverse Recovery Time	$V_{GS} = 0V$, $I_{SD} = 28A$, $dI_F/dt = 100A/\mu s$ (Note 4)	-	279	-	ns
Q_{rr}	Reverse Recovery Charge		-	2.7	-	μC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. L = 1.5mH, $I_{AS} = 28A$, $V_{DD} = 50V$, $R_G = 25\Omega$, Starting $T_J = 25°C$
3. $I_{SD} \le 28A$, $di/dt \le 200A/\mu s$, $V_{DD} \le BV_{DSS}$, Starting $T_J = 25°C$
4. Pulse Test: Pulse width ≤ 300μs, Duty Cycle ≤ 2%
5. Essentially Independent of Operating Temperature Typical Characteristics

Typical Performance Characteristics

Figure 1. On-Region Characteristics

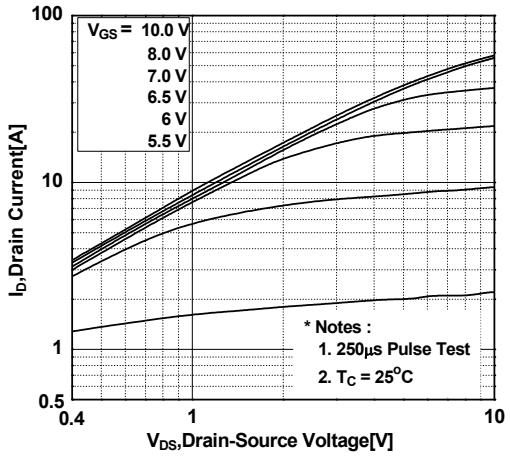


Figure 2. Transfer Characteristics

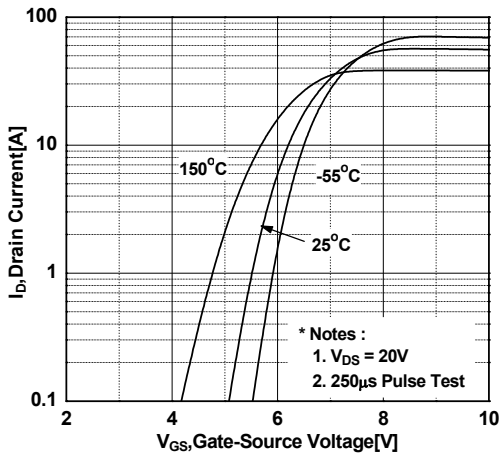


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

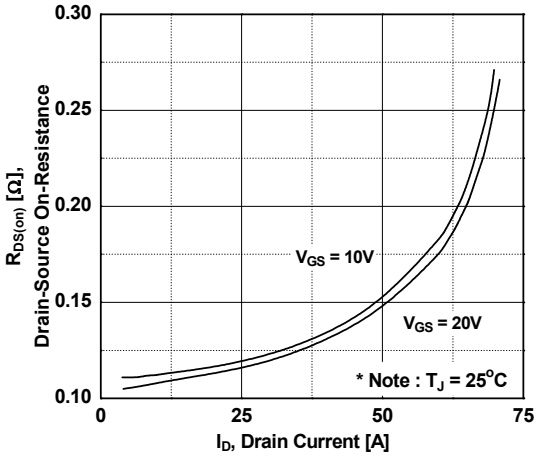


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

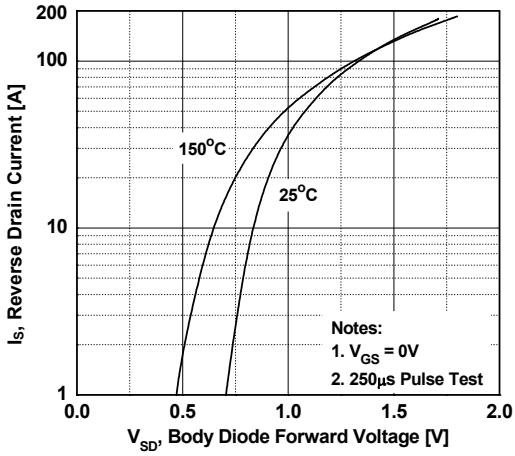


Figure 5. Capacitance Characteristics

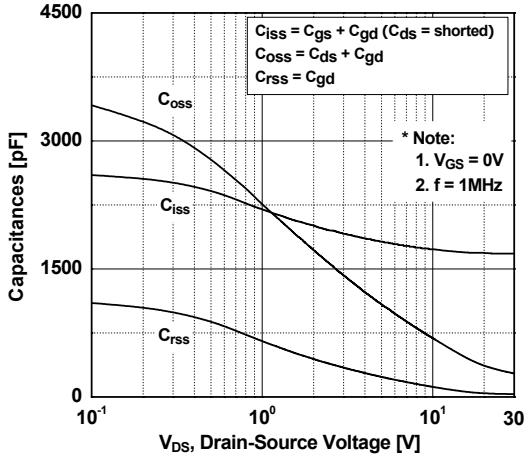
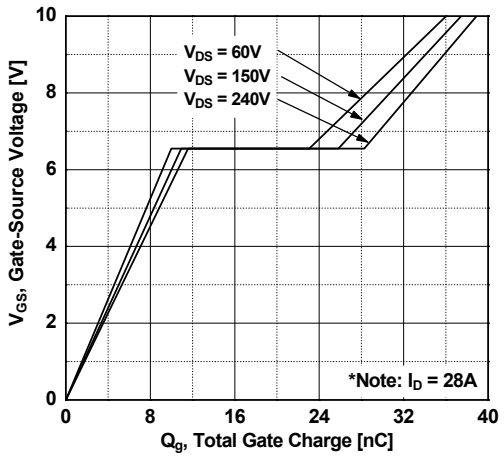


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

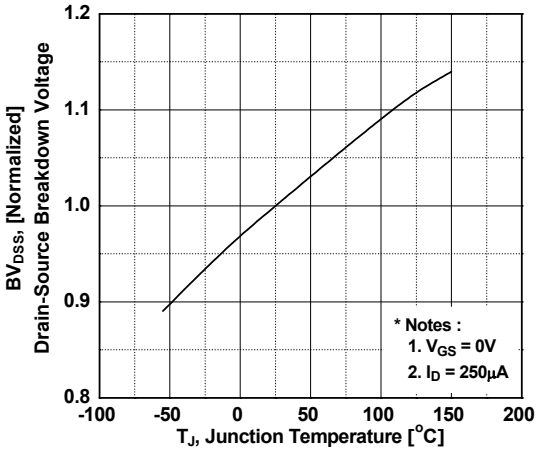


Figure 8. On-Resistance Variation vs. Temperature

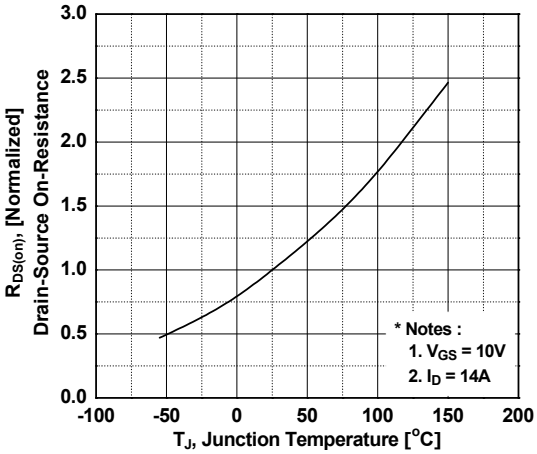


Figure 9. Maximum Safe Operating Area

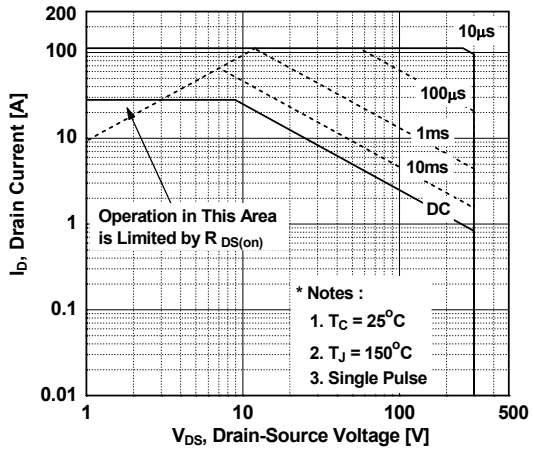


Figure 10. Maximum Drain Current vs. Case Temperature

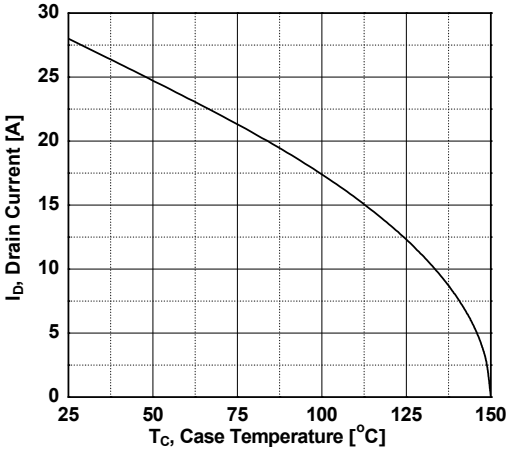
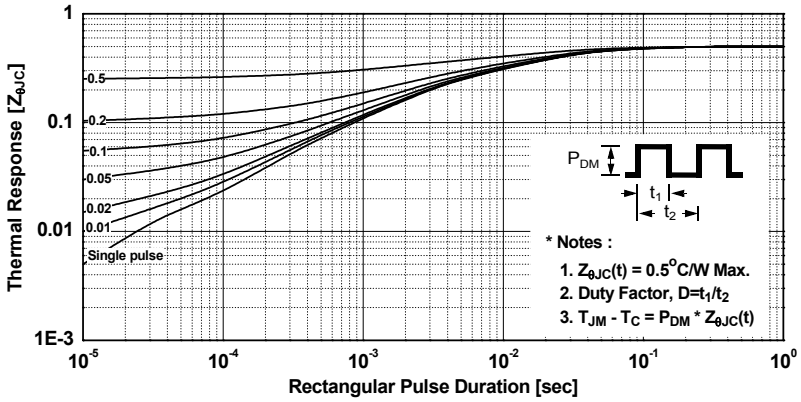
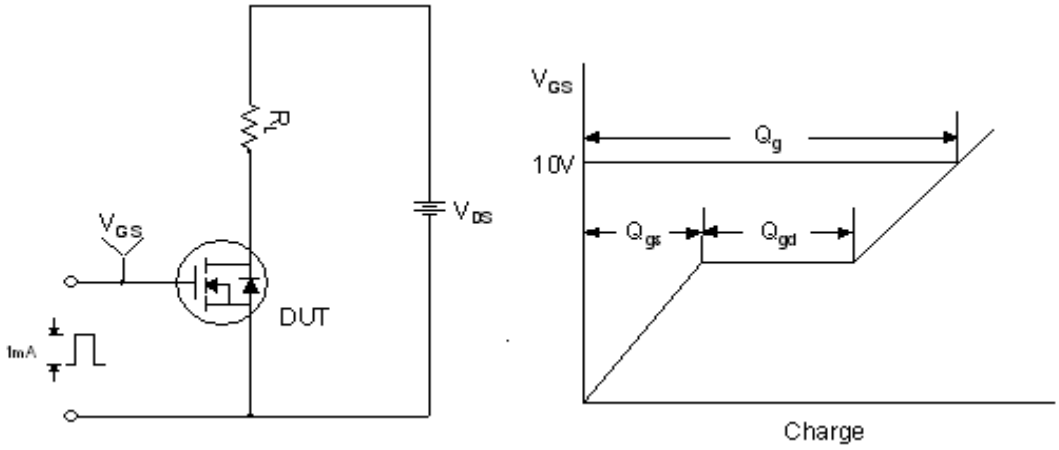


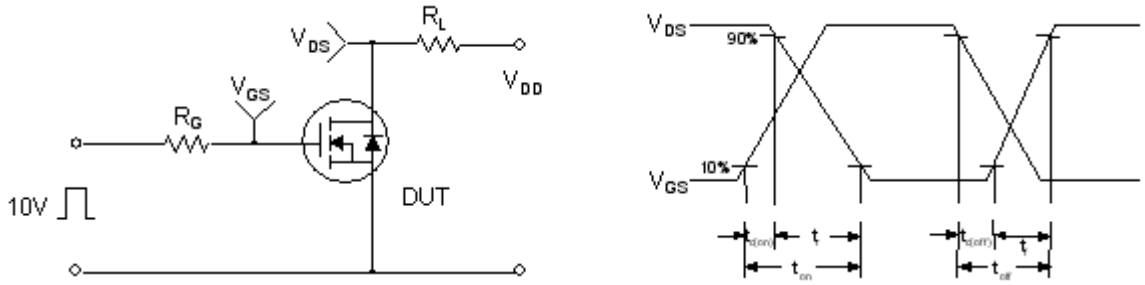
Figure 11. Transient Thermal Response Curve



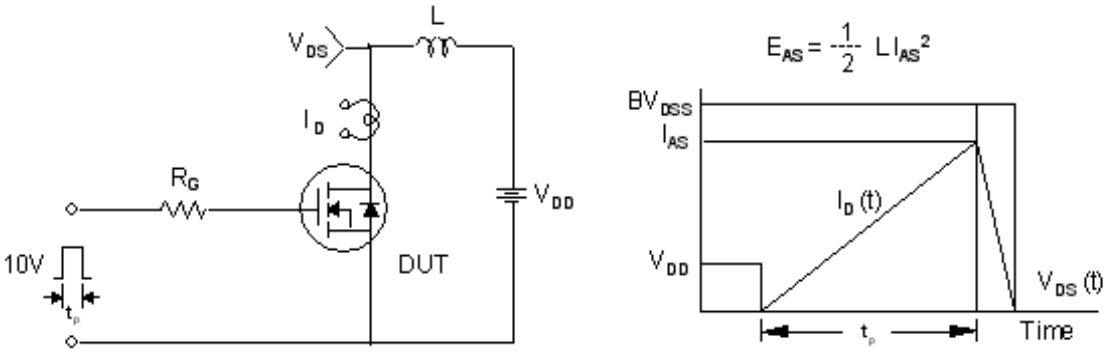
Gate Charge Test Circuit & Waveform



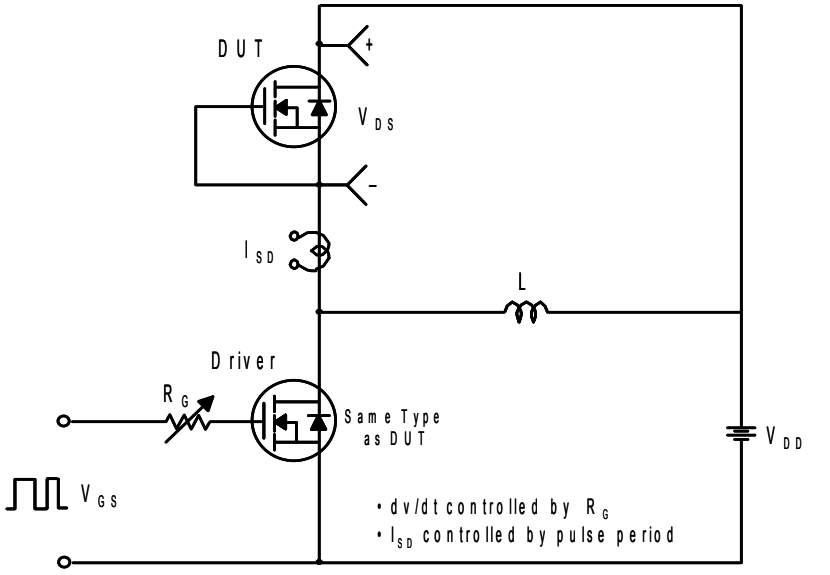
Resistive Switching Test Circuit & Waveforms

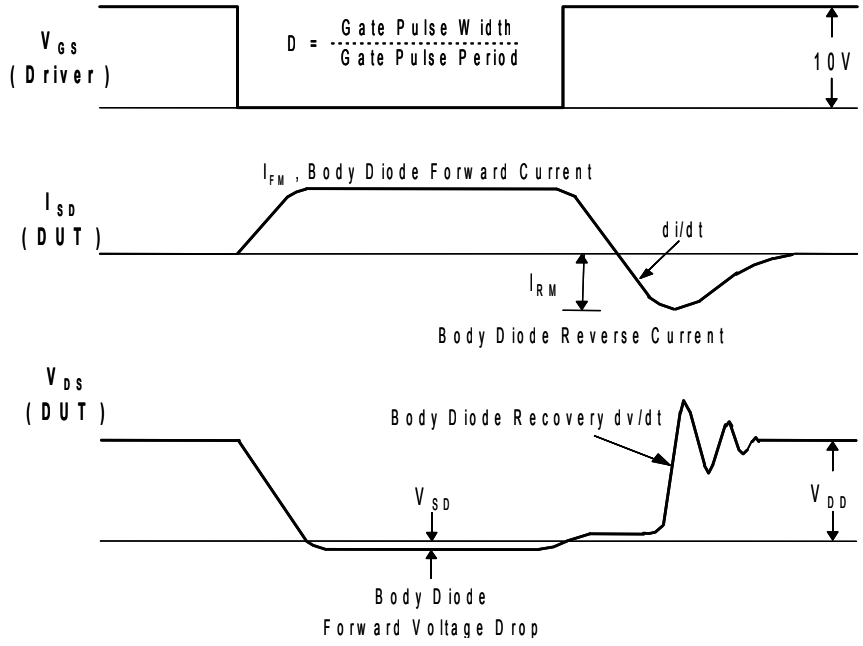


Unclamped Inductive Switching Test Circuit & Waveforms



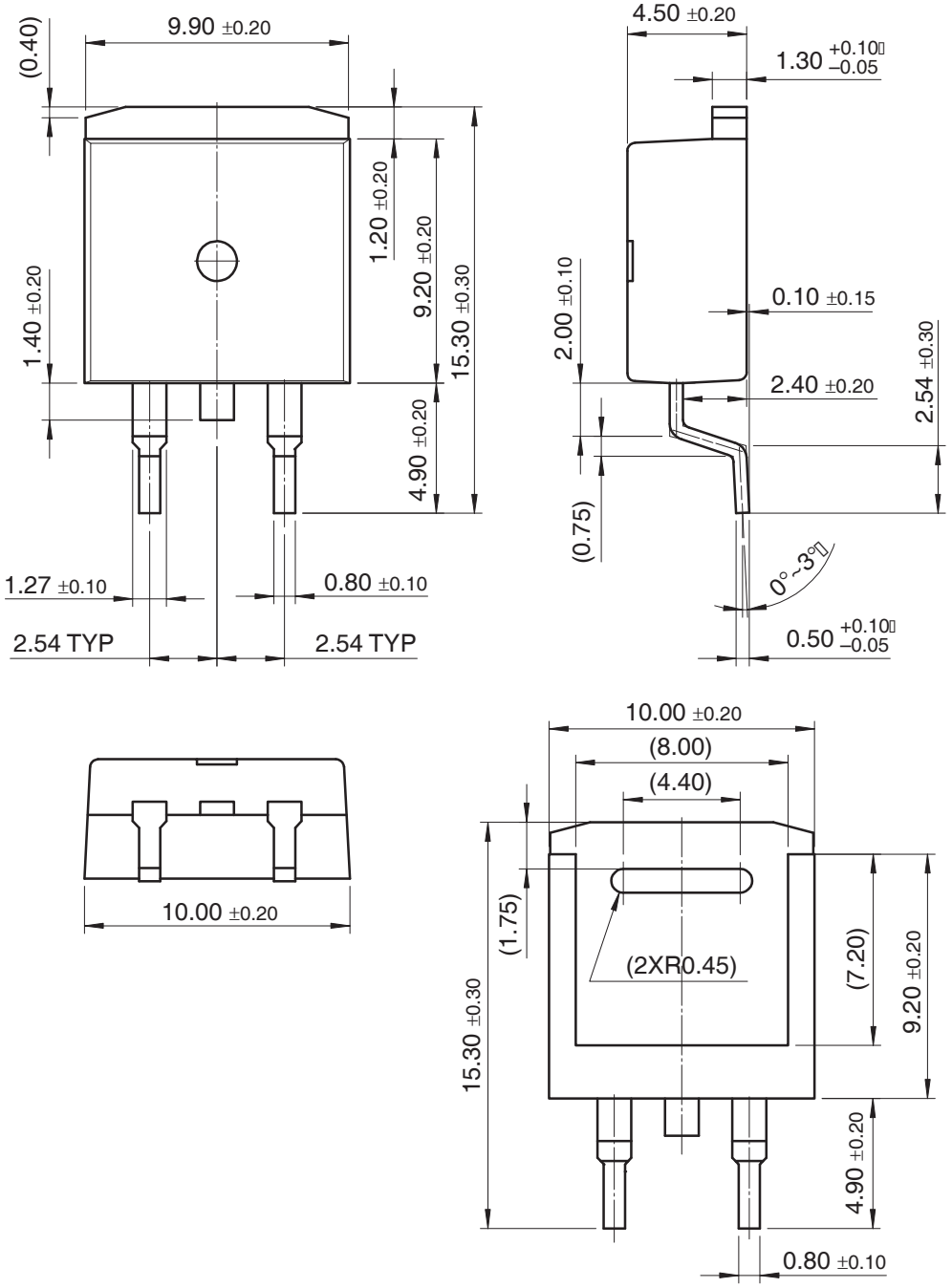
Peak Diode Recovery dv/dt Test Circuit & Waveforms





Mechanical Dimensions

D^2PAK



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